HM101494 Series

16384-Words × 4-Bit Fully Decoded Random Access Memory

■ DESCRIPTION

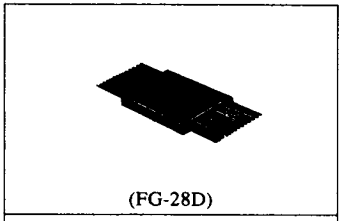
The HM101494 is ECL 100K compatible, 16384-words by 4-bits read/write random access memory developed for high speed systems such as scratch pads and control/buffer storage.

■ FEATURES

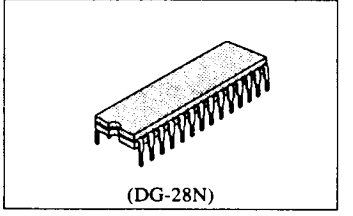
- 16384 × 4 Bit Organization
- Fully Compatible with 100K ECL Level
- Address Access Time . . . . . .10/12ns (max.)
- Write Pulse Width . . . . . .6/8ns (min.)
- Low Power Dissipation . . . . . .750mW (typ.)
- Output Obtainable by Wired-OR (Open Emitter)

■ ORDERING INFORMATION

Type No.	Access Time	Package
HM101494-10 HM101494-12	10ns 12ns	400 mil 28 pin Cerdip (DG-28N)
HM101494F-10 HM101494F-12	10ns 12ns	28 pin Ceramic Flat (FG-28D)

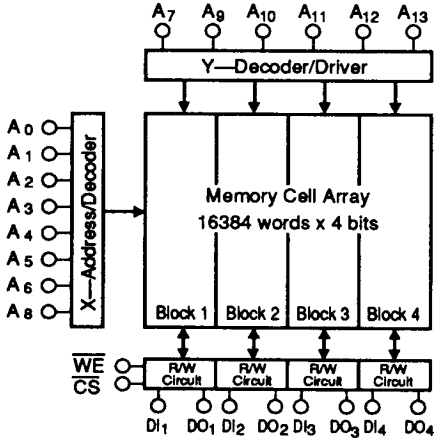


(FG-28D)

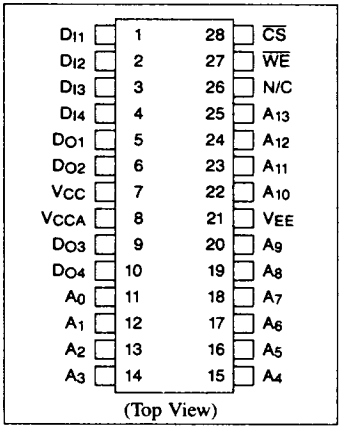


(DG-28N)

■ BLOCK DIAGRAM



■ PIN ARRANGEMENT



(Top View)

■ FUNCTION TABLE

Input			Output	Mode
$\overline{CS}$	$\overline{WE}$	D_{in}		
H	X	X	L	Not Selected
L	L	L	L	Write "0"
L	L	H	L	Write "1"
L	H	X	D_{out}*	Read

NOTES: X = Irrelevant;
* = Read out noninvert

■ ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Item	Symbol	Rating	Unit
Supply Voltage	V_{EE} to V_{CC}	+0.5 to Θ7.0	V
Input Voltage	V_{in}	+0.5 to V_{EE}	V
Output Current	I_{out}	Θ30	mA
Storage Temperature	T_{stg}	Θ65 to +150	°C
Storage Temperature	$T_{stg(bias)}$(1)	Θ55 to +125	°C

NOTES: 1. Under bias.
2. Ceramic flat . . . T_C, Cerdip . . . T_a.

■ ELECTRICAL CHARACTERISTICS

• **DC Characteristics** (V_{EE} = -5.2V, R_L = 50Ω to -2.0V(2), T_a = 0 to +85°C, air flow exceeding 2m/sec.(2), T_C = 0 to +85°C)

Item	Symbol	Test Condition		Min.(B)	Typ.	Max.(A)	Unit
Output Voltage	V_{OH}	V_{in} = V_{IHA} or V_{ILB}		Θ1025	Θ955	Θ880	mV
	V_{OL}			Θ1810	Θ1715	Θ1620	mV
Output Threshold Voltage	V_{OHC}	V_{in} = V_{IHB} or V_{ILA}		Θ1035	—	—	mV
	V_{OLC}			—	—	Θ1610	mV
Input Voltage	V_{IH}	Guaranteed Input Voltage High/Low for All Inputs		Θ1165	—	Θ880	mV
	V_{IL}			Θ1810	—	Θ1475	mV
Input Current	I_{IH}	V_{in} = V_{IHA}		—	—	220	μA
	I_{IL}	V_{in} = V_{ILB}	$\overline{CS}$	0.5	—	170	μA
			Others	Θ50	—	—	
Supply Current	I_{EE}	All Inputs and Outputs Open		Θ180	—	—	mA

• **AC Characteristics** (V_{EE} = -5.2V ± 5%(2), T_a = 0 to +85°C, air flow exceeding 2m/sec.(2), T_C = 0 to +85°C)

1. Read Mode

Item	Symbol	Test Condition	HM101494-10			HM101494-12			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Chip Select Access Time	t_{ACS}		—	—	6	—	—	8	ns
Chip Select Recovery Time	t_{RCS}		—	—	6	—	—	8	ns
Address Access Time	t_{AA}		—	—	10	—	—	12	ns

2. Write Mode

Item	Symbol	Test Condition	HM101494-10			HM101494-12			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Write Pulse Width	t_W	t_{WSA} = t_{WSA} min.	6	—	—	8	—	—	ns
Data Setup Time	t_{WSD}		2	—	—	2	—	—	ns
Data Hold Time	t_{WHD}		2	—	—	2	—	—	ns
Address Setup Time	t_{WSA}	t_W = t_W min.	2	—	—	2	—	—	ns
Address Hold Time	t_{WHA}		2	—	—	2	—	—	ns
Chip Select Setup Time	t_{WSCS}		2	—	—	2	—	—	ns
Chip Select Hold Time	t_{WHCS}		2	—	—	2	—	—	ns
Write Disable Time	t_{WS}		—	—	6	—	—	8	ns
Write Recovery Time	t_{WR}		—	—	12	—	—	14	ns

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3. Rise/Fall Time

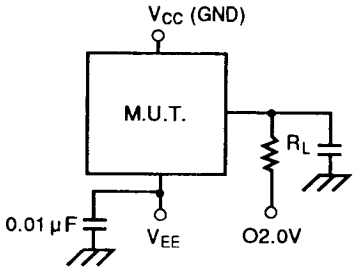
Item	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Output Rise Time	t_r		—	2	—	ns
Output Fall Time	t_f		—	2	—	ns

4. Capacitance

Item	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Input Capacitance	C_{in}	$\overline{WE}$, $\overline{CS}$, D_{I1}, D_{I2}	—	5	—	pF
		Others	—	3	—	pF
Output Capacitance	C_{out}		—	3	—	pF

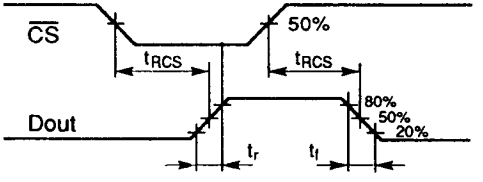
■ TEST CIRCUIT AND WAVEFORMS

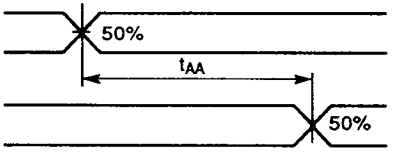
1. Loading Condition



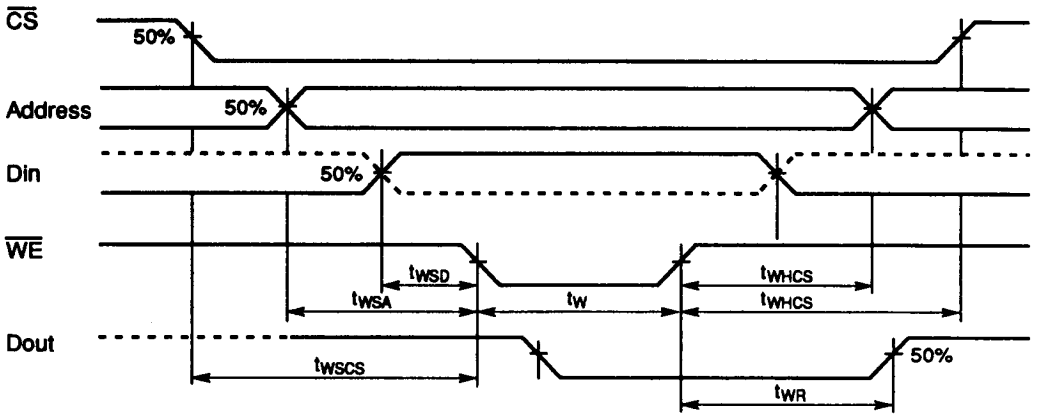
2. Input Pulse

3. Read Mode





4. Write Mode



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